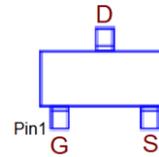
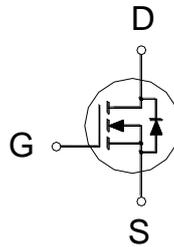


PRODUCT SUMMARY

$V_{(BR)DSS}$	$R_{DS(ON)}$	I_D
60V	88mΩ	2A



G. GATE
D. DRAIN
S. SOURCE



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ °C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNITS
Drain-Source Voltage		V_{DS}	60	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	$T_C = 25\text{ °C}$	I_D	2	A
	$T_C = 70\text{ °C}$		1.6	
Pulsed Drain Current ¹		I_{DM}	11	
Power Dissipation	$T_A = 25\text{ °C}$	P_D	0.78	
	$T_A = 70\text{ °C}$		0.5	
Operating Junction & Storage Temperature Range		T_j, T_{stg}	-55 to 150	°C

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNITS
Junction-to-Ambient ²	$R_{\theta JA}$		159	°C / W

¹Pulse width limited by maximum junction temperature.

²The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25\text{ °C}$.

ELECTRICAL CHARACTERISTICS ($T_J = 25\text{ °C}$, Unless Otherwise Noted)

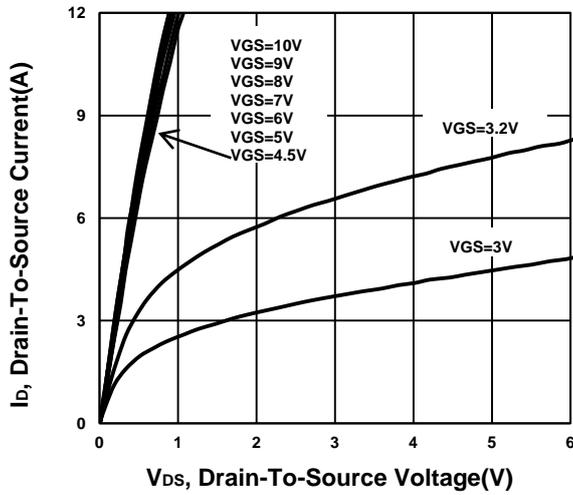
PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	60			V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	1.3	1.9	2.3	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0V, V_{GS} = \pm 20V$			±100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 48V, V_{GS} = 0V$			1	μA
		$V_{DS} = 40V, V_{GS} = 0V, T_J = 55\text{ °C}$			10	
Drain-Source On-State Resistance ¹	$R_{DS(ON)}$	$V_{GS} = 4.5V, I_D = 2A$		71	108	mΩ
		$V_{GS} = 10V, I_D = 2A$		59	88	

Forward Transconductance ¹	g_{fs}	$V_{DS} = 5V, I_D = 2A$		10		S
DYNAMIC						
Input Capacitance	C_{iss}	$V_{GS} = 0V, V_{DS} = 25V, f = 1MHz$	228	286	343	pF
Output Capacitance	C_{oss}		30	38	45.6	
Reverse Transfer Capacitance	C_{rss}		16	28	39	
Total Gate Charge ²	Q_g	$V_{DS} = 30V, V_{GS} = 10V, I_D = 2A$	6.8	8.5	10.2	nC
Gate-Source Charge ²	Q_{gs}		0.6	0.8	1	
Gate-Drain Charge ²	Q_{gd}		2	3.3	4.6	
Turn-On Delay Time ²	$t_{d(on)}$	$V_{DS} = 30V, I_D \cong 2A, V_{GS} = 10V, R_{GEN} = 6\Omega$		8.3		nS
Rise Time ²	t_r			10		
Turn-Off Delay Time ²	$t_{d(off)}$			20		
Fall Time ²	t_f			4.5		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS ($T_J = 25^\circ C$)						
Continuous Current	I_S				0.6	A
Forward Voltage ¹	V_{SD}	$I_F = 2A, V_{GS} = 0V$			1.2	V
Reverse Recovery Time	t_{rr}	$I_F = 2A, di_F/dt = 100A / \mu S$	9	18	27	nS
Reverse Recovery Charge	Q_{rr}		5	10	15	nC

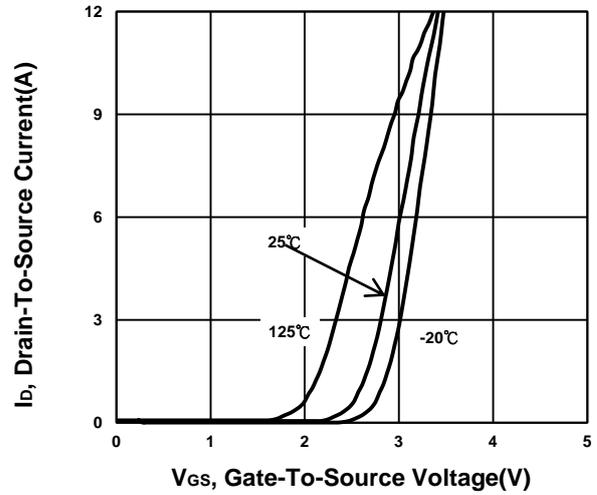
¹Pulse test : Pulse Width $\leq 300 \mu sec$, Duty Cycle $\leq 2\%$.

²Independent of operating temperature.

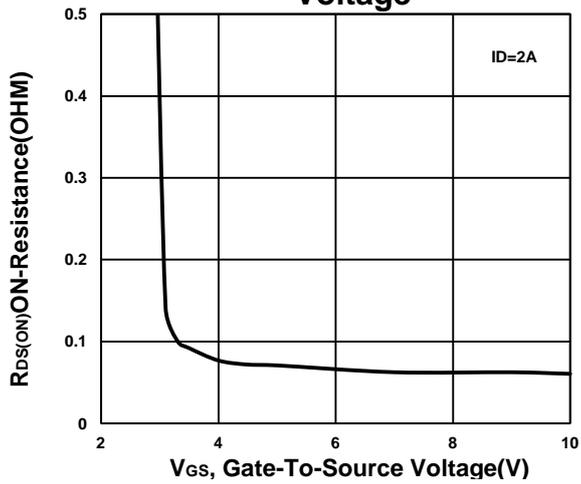
Output Characteristics



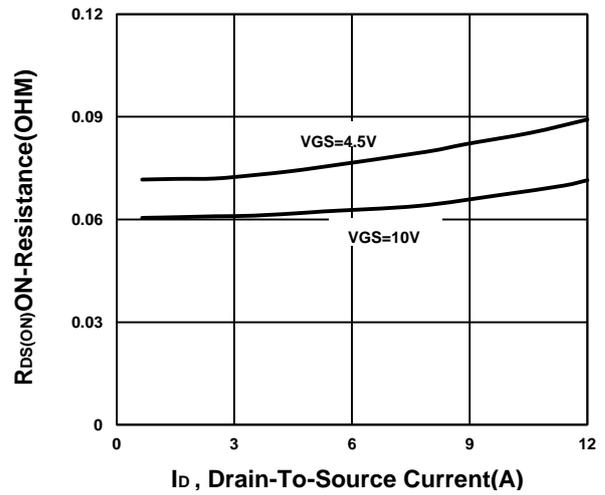
Transfer Characteristics



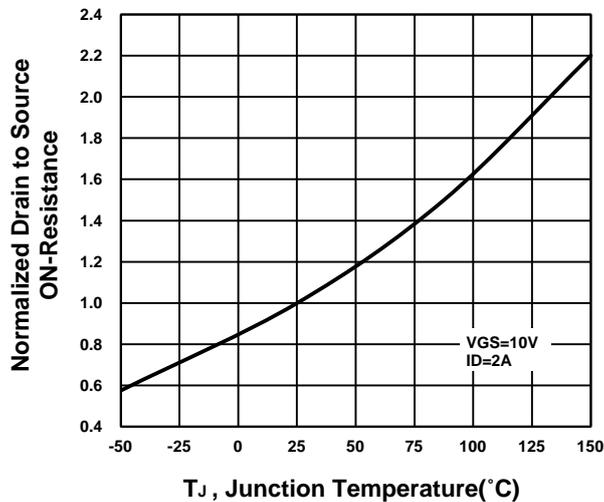
On-Resistance VS Gate-To-Source Voltage



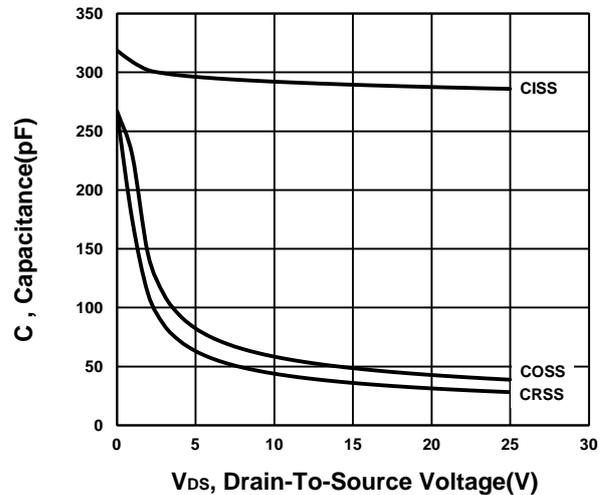
On-Resistance VS Drain Current



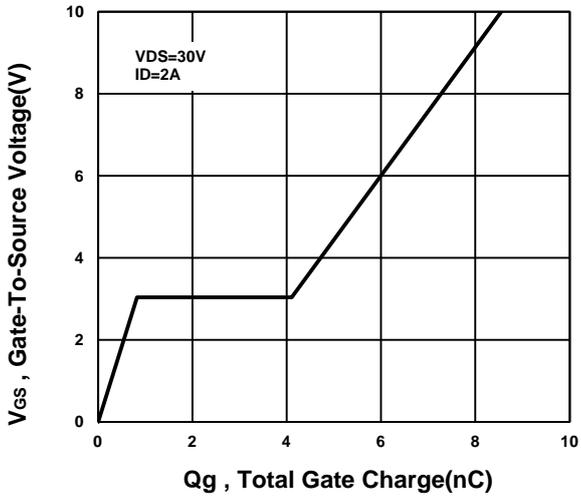
On-Resistance VS Temperature



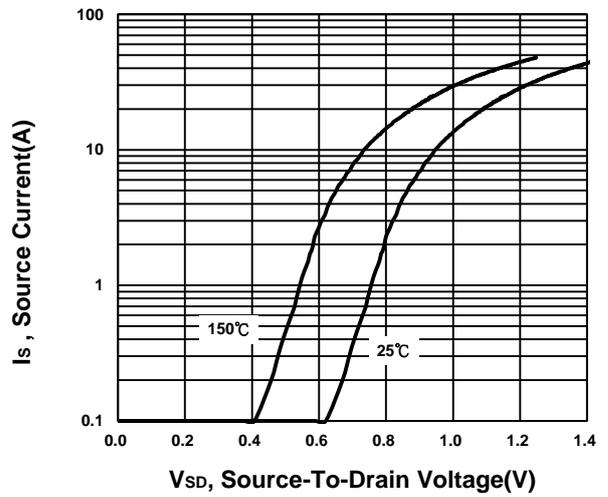
Capacitance Characteristic



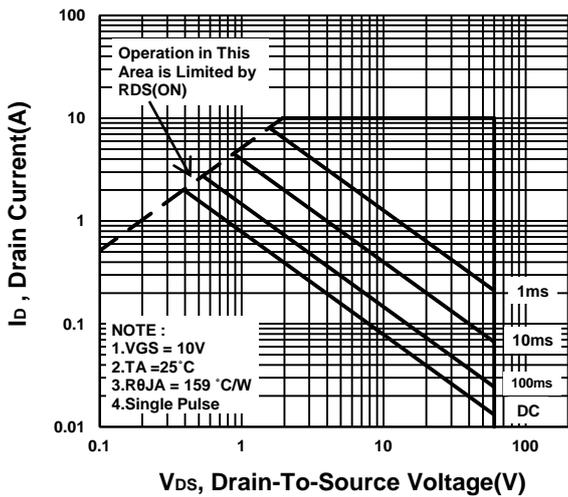
Gate charge Characteristics



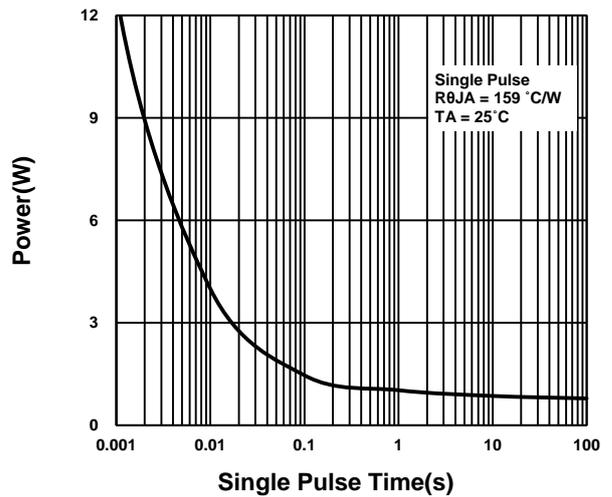
Source-Drain Diode Forward Voltage



Safe Operating Area



Single Pulse Maximum Power Dissipation



Transient Thermal Response Curve

